

Features:

- 120V Schottky Diode
- Zero Reverse Recovery Current
- High Frequency Operation
- Positive Temperature Coefficient
- Temperature independent

Switching

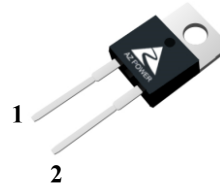
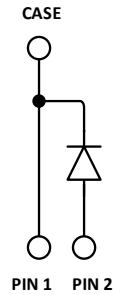
Benefits:

- Unipolar Rectifier
- Minimal switching loss
- Higher Efficiency
- Low cooling requirement

Symbol	Value	Unit
V_{RRM}	1200	V
I_F ($T_C = 163^\circ\text{C}$)	2	A
Q_C	12	nC

Applications:

- Switch Mode Power Supply
- Booster diodes in PFC, DC/DC
- AC/DC converters

Outline

TO-220-2L
Circuit

Maximum Ratings

Symbol	Parameter	Value	Unit	Test Conditions
V_R	DC Peak Reverse Voltage	1200	V	$T_J = 25^\circ\text{C}$
V_{RRM}	Repetitive Peak Reverse	1200	V	$T_J = 25^\circ\text{C}$
V_{RSM}	Surge Peak Reverse Voltage	1300	V	$T_J = 25^\circ\text{C}$
I_F	Continuous Forward Current	9	A	$T_C = 25^\circ\text{C}$
		4		$T_C = 135^\circ\text{C}$
		2		$T_C = 163^\circ\text{C}$
I_{FRM}	Repetitive Peak Forward Surge Current	19	A	$T_C = 25^\circ\text{C}, T_p = 10\text{ms}, \text{Half Sine Wave}$
		16		$T_C = 125^\circ\text{C}, T_p = 10\text{ms}, \text{Half Sine Wave}$
I_{FSM}	Non-Repetitive Peak Forward Surge Current	27	A	$T_C = 25^\circ\text{C}, T_p = 10\text{ms}, \text{Half Sine Wave}$
		25		$T_C = 125^\circ\text{C}, T_p = 10\text{ms}, \text{Half Sine Wave}$
P_D	Power Dissipation	55	W	$T_C = 25^\circ\text{C}$
		18.5		$T_C = 125^\circ\text{C}$
$T_{J,max}$	Operating Junction Temperature	175	$^\circ\text{C}$	
T_{stg}	Storage Temperature Range	-55 to 175	$^\circ\text{C}$	

Thermal characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit
R_{thJC}	Thermal resistance		2.7		°C/W

Electrical Characteristics

Symbol	Parameter	Value			Unit	Test Conditions
		Min.	Typ.	Max.		
V_{DC}	DC Blocking Voltage	1200			V	$I_R = 100\mu A, T_J = 25^\circ C$
V_F	Forward Voltage		1.5 2.3	1.8 2.6	V	$I_F = 2A, T_J = 25^\circ C$ $I_F = 2A, T_J = 175^\circ C$
I_R	Reverse Current		1 2	50 250	μA	$V_R = 1200V, T_J = 25^\circ C$ $V_R = 1200V, T_J = 175^\circ C$
Q_C	Total Capacitive Charge		12		nC	$I_F = 2A, dI/dt = 200A/\mu s$ $T_J = 25^\circ C, V_R = 800V$
C	Total Capacitance		132 20 18		pF	$V_R = 1V, T_J = 25^\circ C, f = 1 MHz$ $V_R = 400V, T_J = 25^\circ C, f = 1 MHz$ $V_R = 800V, T_J = 25^\circ C, f = 1 MHz$

Typical Performance

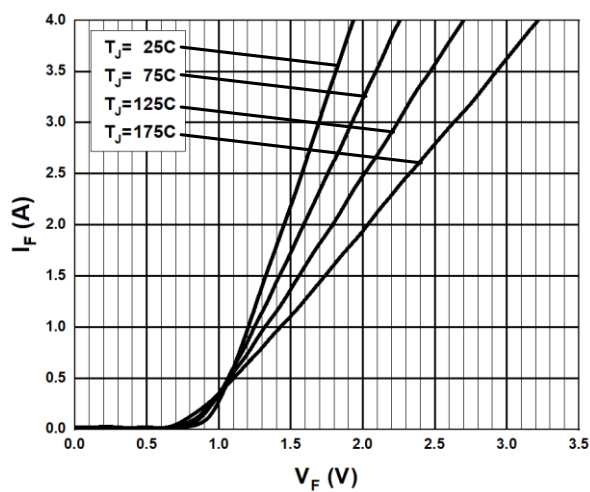


Fig. 1 Forward Characteristics

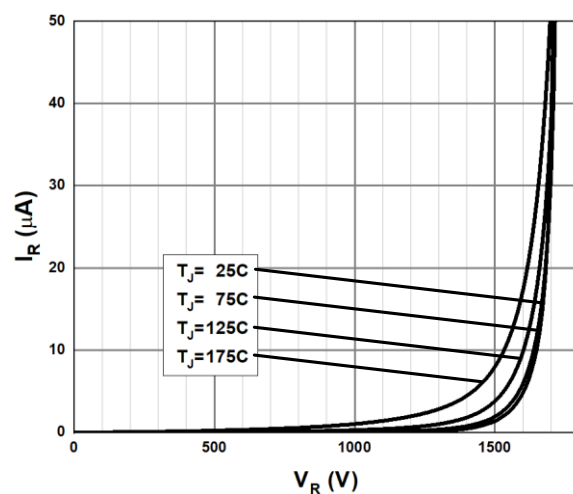


Fig. 2 Reverse Characteristics

Typical Performance

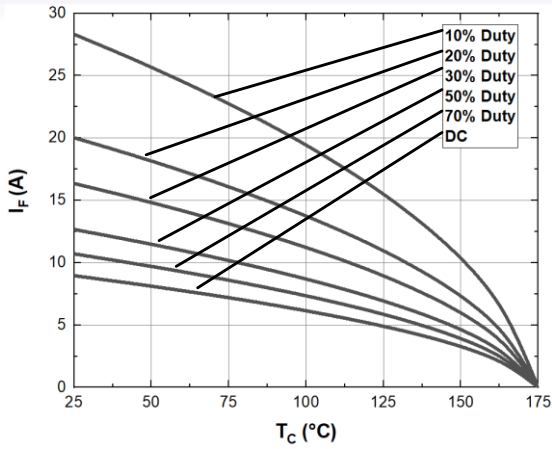


Fig. 3 Current Derating

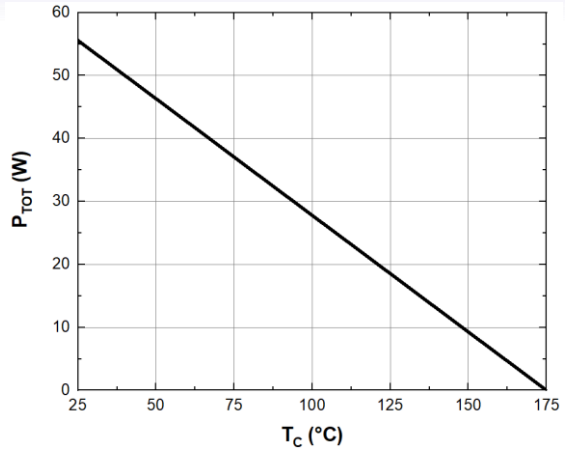


Fig. 4 Power Derating

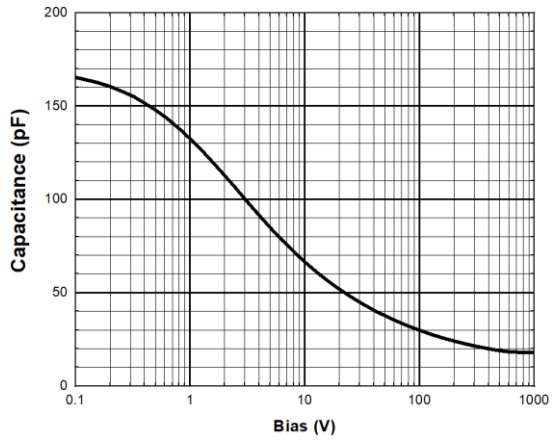


Fig. 5 Capacitance vs. Reverse Voltage

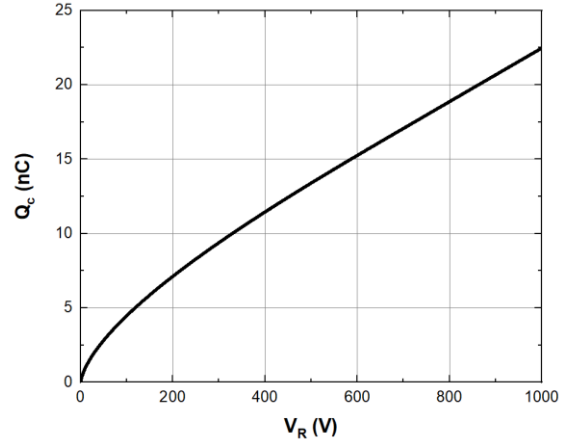


Fig. 6 Recovery Charge vs. Reverse Voltage

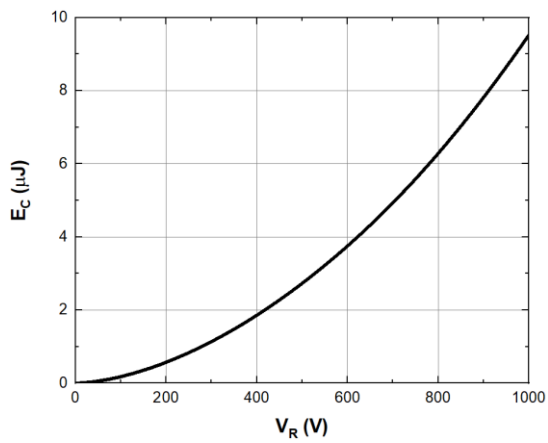


Fig. 7 Capacitance stored Energy

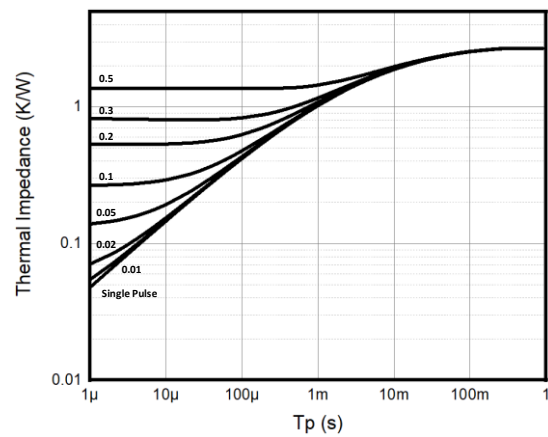
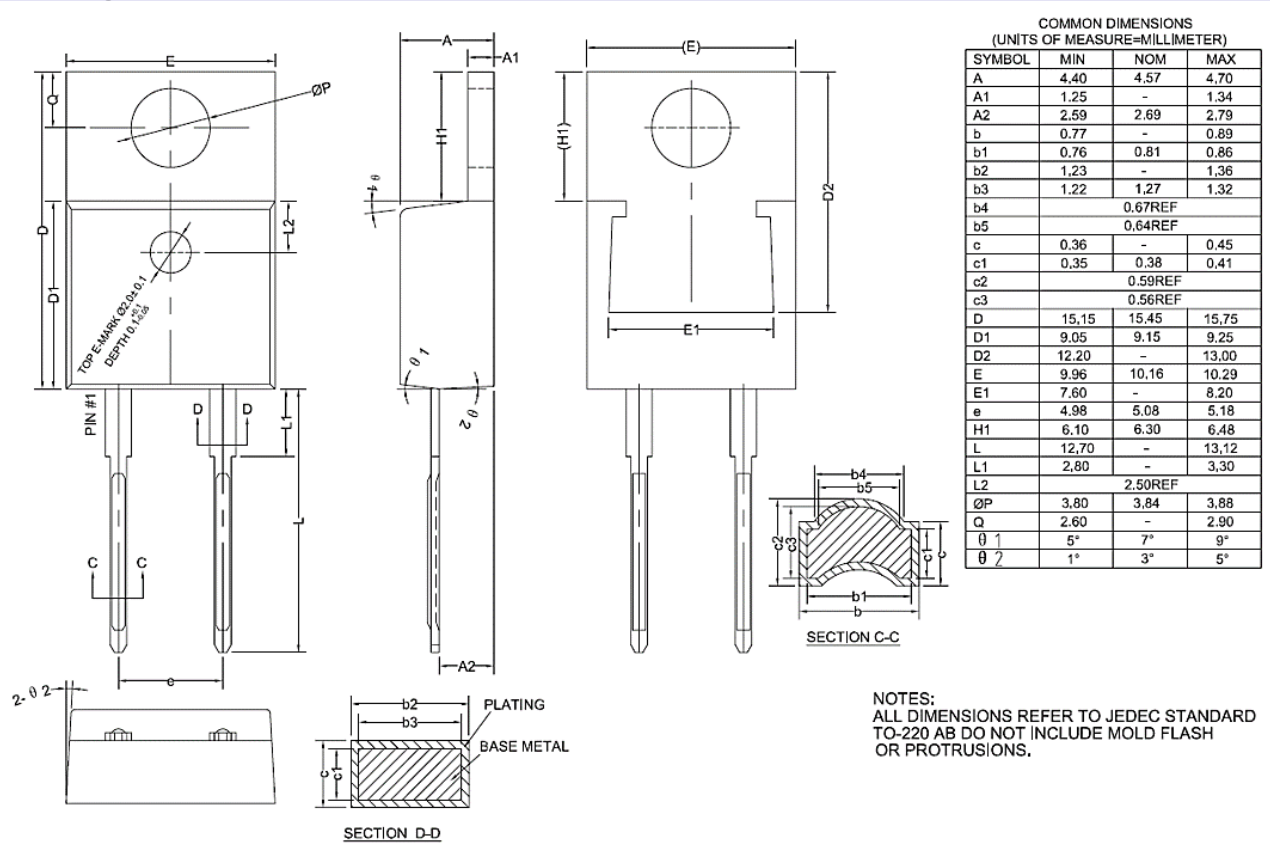


Fig. 8 Thermal impedance

Package TO-220-2L (Unit: mm)



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